Diagnosing Adhesion and Cohesion for BEOL Reliability: From Dieseals and Crack Stops to Cu and Low k

Low k Research
Max Gage, Markus Ong
Taek-Soo Kim, Nathan Stein

Chip/Package Interactions
Andrew Kearney, Bree Sharratt, Zhouyuan Zhu

Front End Structures
Ryan Birringer

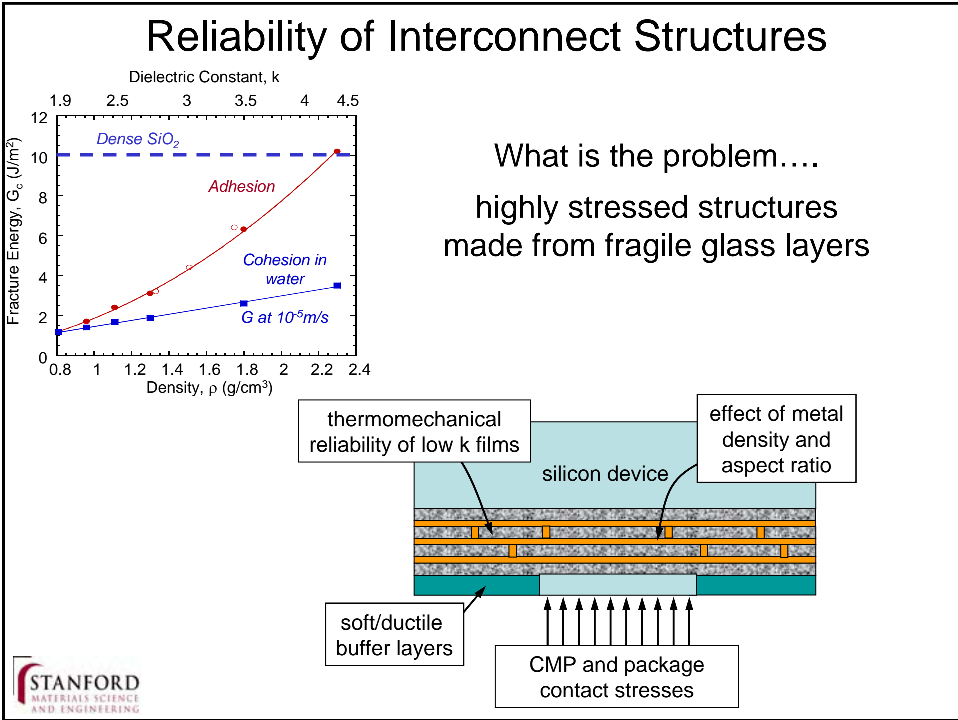
Reinhold H. Dauskardt
(dauskardt@stanford.edu)

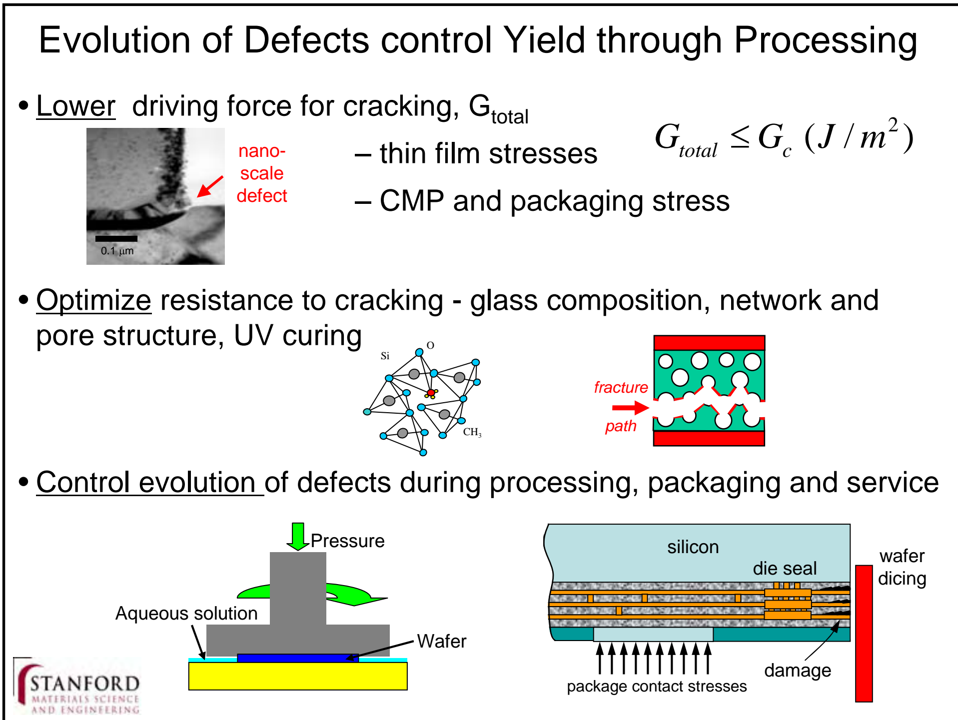
Collaborators at INTEL, AMD, IBM, Applied Materials, ASM and JSR.

Work supported by the SRC, DOE, Device, Equipment and Materials Companies.

Outline

- Mechanical Reliability of Low-k Materials
  - what is the problem?
  - fracture properties and scaling with density/dielectric constant
- UV Curing Effects on Mechanical Properties
  - fracture path and effects on cohesive and adhesive properties
  - balancing film stress, modulus and fracture properties
- Non-Uniform UV Curing Phenomena
  - evidence for non-uniform curing
  - likely mechanism associated with UV light interference
- CMP Aqueous Chemistry Effects
  - accelerated cracking in aqueous CMP slurries and cleaning solutions
- Die Seal and Crack Stop Structures
  - fracture mechanics approach to preventing dicing damage
- Summary


Reliability of Interconnect Structures
Dielectric Constant, k
1.9 2.5 3 3.5 4 4.5
Fracture Energy, G_c (J/m^2)
Dense SiO_2
Adhesion
Cohesion in water
G at 10^{-5}m/s
Density, ρ (g/cm^3)
What is the problem….
highly stressed structures made from fragile glass layers
thermomechanical reliability of low k films
effect of metal density and aspect ratio
silicon device
soft/ductile buffer layers
CMP and package contact stresses
STANFORD
MATERIALS SCIENCE AND ENGINEERING


Evolution of Defects control Yield through Processing
• Lower driving force for cracking, G_{total}
$G_{total} \leq G_c \; (J/m^2)$
nano-scale defect
0.1 µm
– thin film stresses
– CMP and packaging stress
• Optimize resistance to cracking - glass composition, network and pore structure, UV curing
Si
O
CH_3
fracture path
• Control evolution of defects during processing, packaging and service
Pressure
Aqueous solution
Wafer
silicon
die seal
wafer dicing
package contact stresses
damage
STANFORD
MATERIALS SCIENCE AND ENGINEERING

Outline

- Mechanical Reliability of Low-k Materials
  - what is the problem?
  - fracture properties and scaling with density/dielectric constant
- UV Curing Effects on Mechanical Properties
  - fracture path and effects on cohesive and adhesive properties
  - balancing film stress, modulus and fracture properties
- Non-Uniform UV Curing Phenomena
  - evidence for non-uniform curing
  - likely mechanism associated with UV light interference
- CMP Aqueous Chemistry Effects
  - accelerated cracking in aqueous CMP slurries and cleaning solutions
- Die Seal and Crack Stop Structures
  - fracture mechanics approach to preventing dicing damage
- Summary

Experimental Methods

Glass Structure

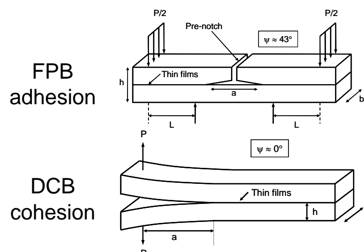
- ^{29}Si and ^{13}C magic angle spinning NMR (3.2 mm MAS rotor, 12-13 KHz spinning rates, 9.4 Tesla magnet)
- FTIR

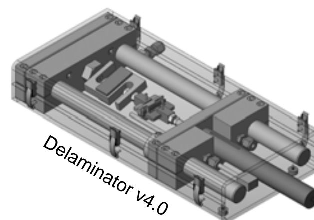
Fracture Mechanics Testing

- Four Point Bend (FPB) and Double Cantilever Beam (DCB) geometries

FPB adhesion

DCB cohesion





Fracture Surface Morphology/Composition

- AFM, XPS

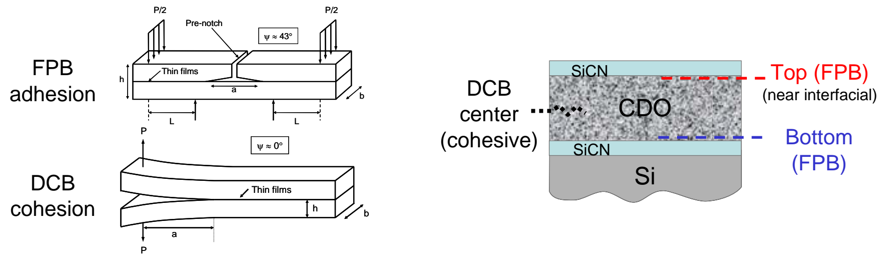
Experimental Methods

Glass Structure

- ^{29}Si and ^{13}C magic angle spinning NMR (3.2 mm MAS rotor, 12-13 KHz spinning rates, 9.4 Tesla magnet)
- FTIR

Fracture Mechanics Testing

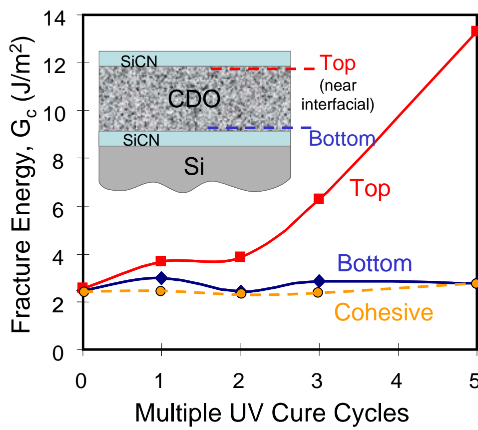
- Four Point Bend (FPB) and Double Cantilever Beam (DCB) geometries

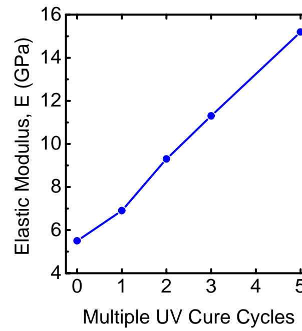


Fracture Surface Morphology/Composition

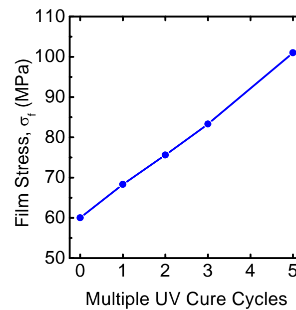
- AFM, XPS

Role of UV Cure on Mechanical Properties



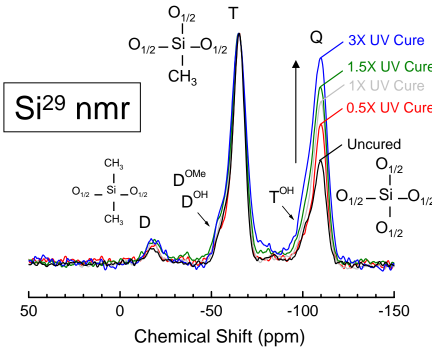


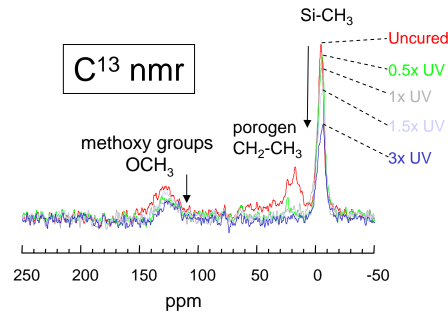
Treatment	Dielectric Constant	Elastic Modulus, $\bar{E}_f$ (GPa)	Residual Film Stress, σ_f (MPa)	Crack Driving Force, G (J/m^2)	Cohesive Fracture, G_c (J/m^2)
none	2.62	5.5	60	0.287	2.50
UVx1	2.59	6.9	68.3	0.296	2.40
UVx2	2.62	9.3	75.6	0.269	2.36
UVx3	2.66	11.3	83.3	0.269	2.34
UVx5	2.72	15.2	101	0.294	2.66



UV Curing Effects on Glass Structure

Porous DEMS (k = 2.5)



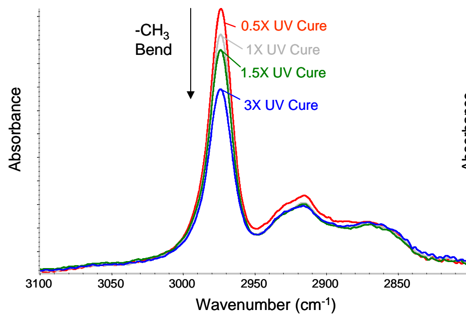


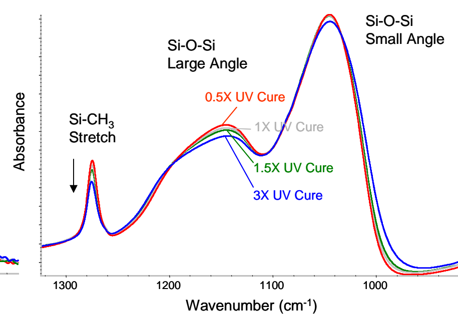
- progressive loss of $–CH_3$ and –OH groups
- Increasing more Si-O-Si bridging bonds

- initial loss of CH_2 groups from porogen
- progressive loss of $Si\text{-}CH_3$ groups
- some loss in C=C groups

Gage, Cui, Al-Bayati, Demos, MacWilliams, M'saad and Dauskardt – 2006.

FTIR Structural Characterization





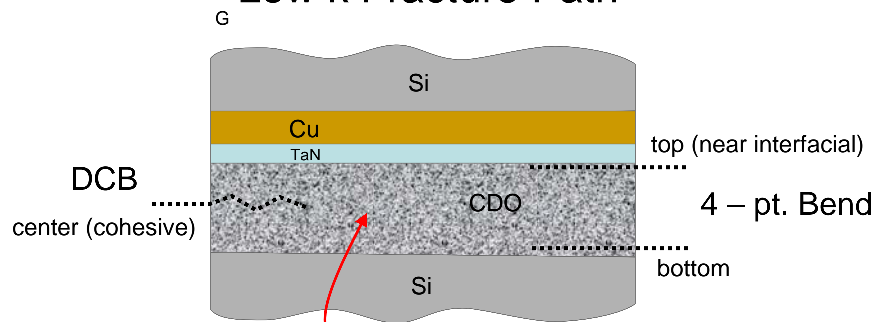
- Progressive reduction of $–CH_3$ with UV curing
- Only minor change in skeleton (reduction in large angle Si-O-Si stretch band)
- No indication of transition to small angle network configuration with cure (insensitivity of the Si-O stretch bands at 1140 cm-1 and 1040 cm-1)
- Improvements in fracture energies not due to rearrangement of the glass backbone but to an increased degree of network connectivity

Gage, Cui, Al-Bayati, Demos, MacWilliams, M'saad and Dauskardt – 2006.

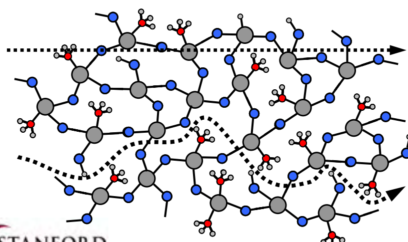
Outline

- Mechanical Reliability of Low-k Materials
  - what is the problem?
  - fracture properties and scaling with density/dielectric constant
- Studies of Glass Network Structure
  - NMR and FTIR reveal glass network structure
  - UV cure reactions and changes in network structure
- UV Curing Effects on Mechanical Properties
  - fracture path and effects on cohesive and adhesive properties
  - balancing film stress, modulus and fracture properties
- Non-Uniform UV Curing Phenomena
  - evidence for non-uniform curing
  - likely mechanism associated with UV light interference
- Summary

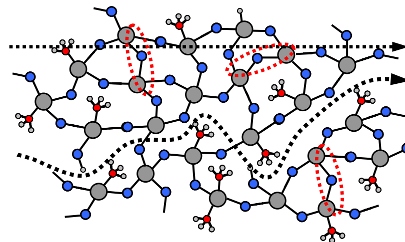
Low k Fracture Path

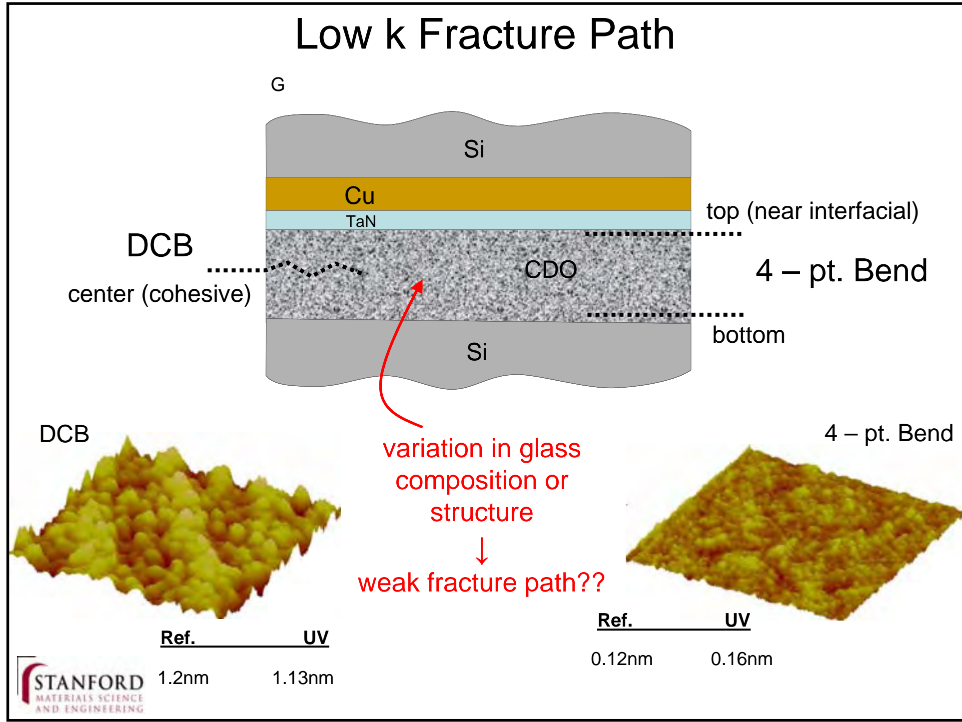


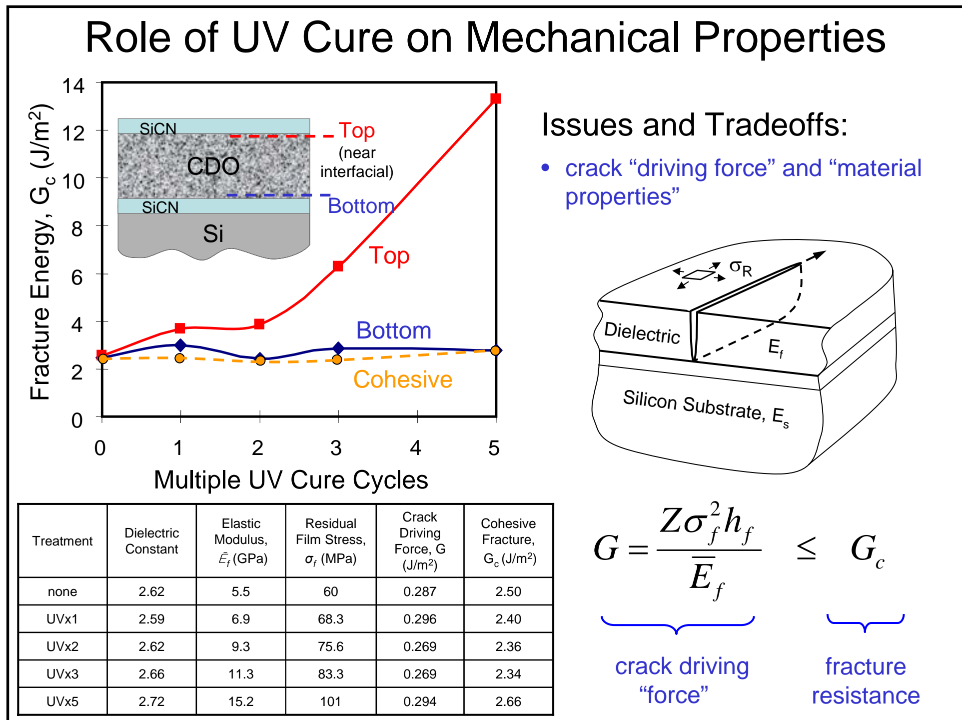
Uncured



Cured

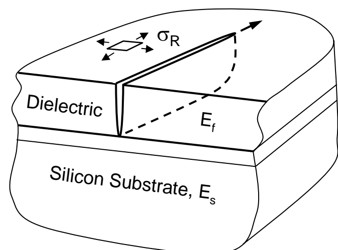






Treatment	Dielectric Constant	Elastic Modulus, $\bar{E}_f$ (GPa)	Residual Film Stress, σ_f (MPa)	Crack Driving Force, G (J/m^2)	Cohesive Fracture, G_c (J/m^2)
none	2.62	5.5	60	0.287	2.50
UVx1	2.59	6.9	68.3	0.296	2.40
UVx2	2.62	9.3	75.6	0.269	2.36
UVx3	2.66	11.3	83.3	0.269	2.34
UVx5	2.72	15.2	101	0.294	2.66

Issues and Tradeoffs

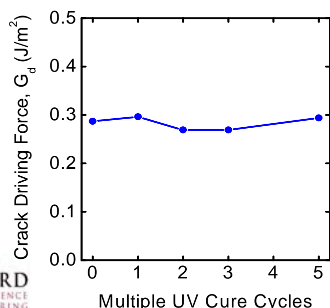


$$G_d = \frac{Z\sigma_f^2 h_f}{\bar{E}_f} \leq G_c$$

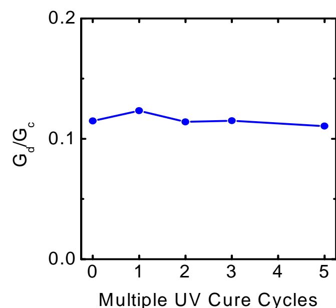
crack driving "force"

fracture resistance

G_d vs. UV Cure Cycles



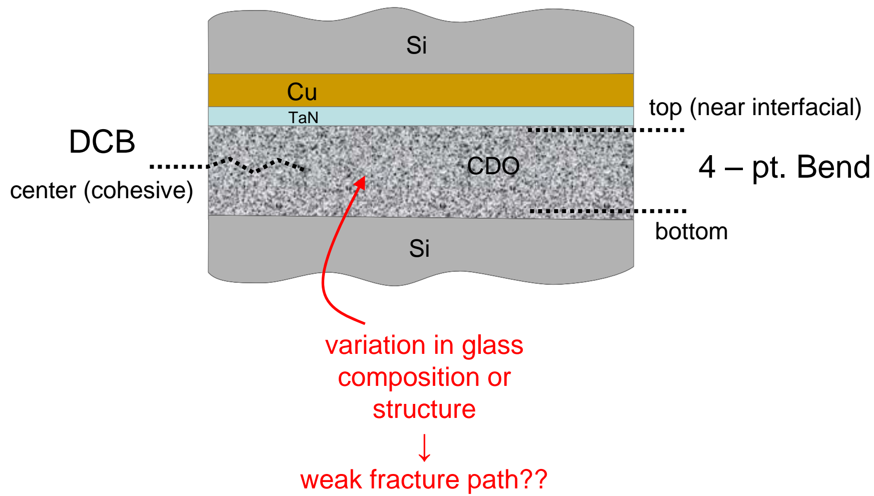
G_d/G_c vs. UV Cure Cycles



Outline

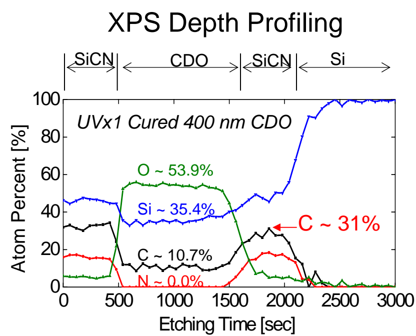
- Mechanical Reliability of Low-k Materials
  - what is the problem?
  - fracture properties and scaling with density/dielectric constant
- UV Curing Effects on Mechanical Properties
  - fracture path and effects on cohesive and adhesive properties
  - balancing film stress, modulus and fracture properties
- Non-Uniform UV Curing Phenomena
  - evidence for non-uniform curing
  - likely mechanism associated with UV light interference
- CMP Aqueous Chemistry Effects
  - accelerated cracking in aqueous CMP slurries and cleaning solutions
- Die Seal and Crack Stop Structures
  - fracture mechanics approach to preventing dicing damage
- Summary

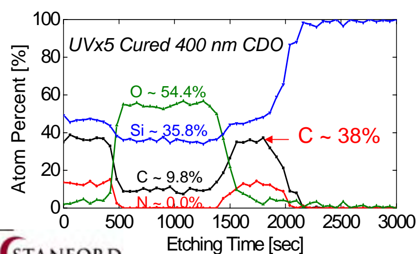
Non-Uniform Curing Phenomena

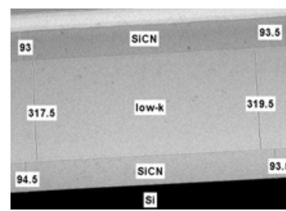


No Evidence of Compositional Variation

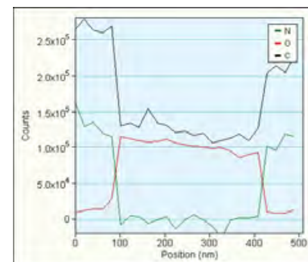
XPS Depth Profiling





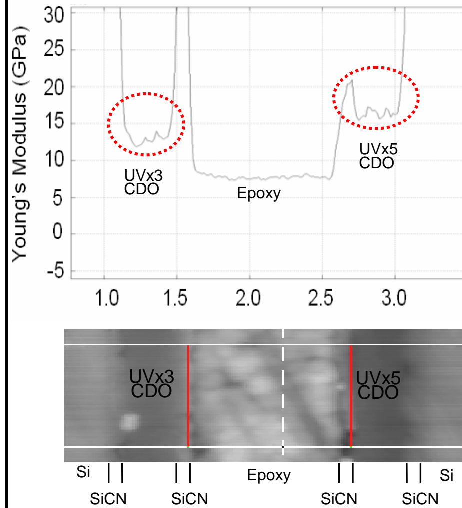


EELS composition profile taken in STEM mode

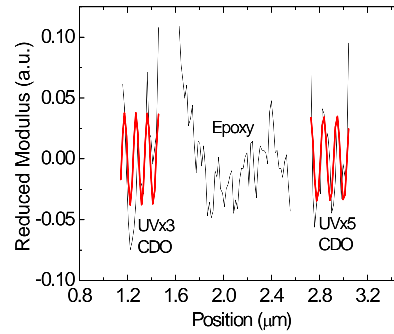


T. Kim, N. Tsuji, N. Kemeling, K. Matsushita, D. Chumakov, E. Zschech, and R. H. Dauskardt, AMC2006.

FM-AFM Measurements of Modulus Variations

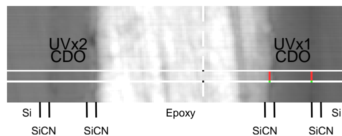


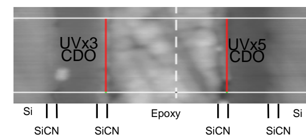
sine wave fitting of modulus variations

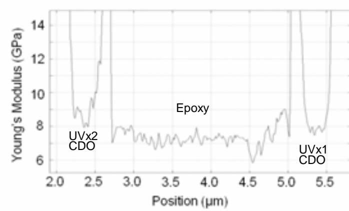


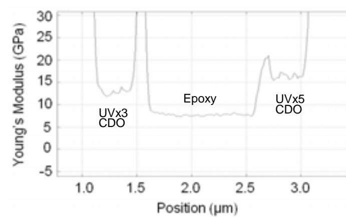
T. Kim, N. Tsuji, N. Kemeling, K. Matsushita, D. Chumakov, E. Zschech, and R. H. Dauskardt, AMC2006.

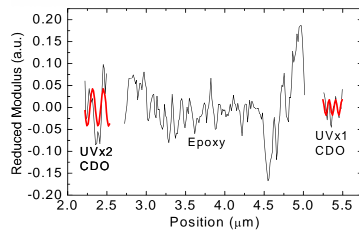
FM-AFM Measurements of Modulus Variations

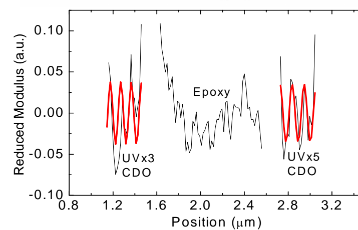












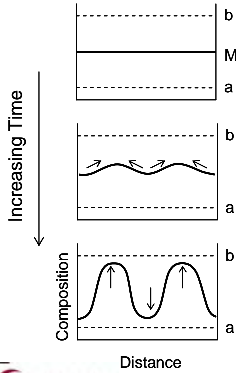
T. Kim, N. Tsuji, N. Kemeling, K. Matsushita, D. Chumakov, E. Zschech, and R. H. Dauskardt, AMC2006.

Possible Causes of Modulus Variation

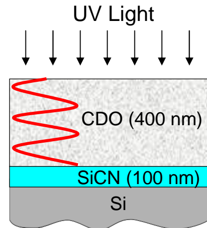
Phase separation

Spinodal decomposition

[Cahn and Hilliard, 1958]



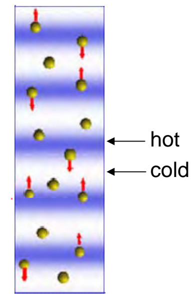
UV light interference



Cured bond density proportional to light intensity

Soret effect

Photothermal heat generated by UV standing wave and activated atoms migrate.



Standing-Wave Effects during UV Curing

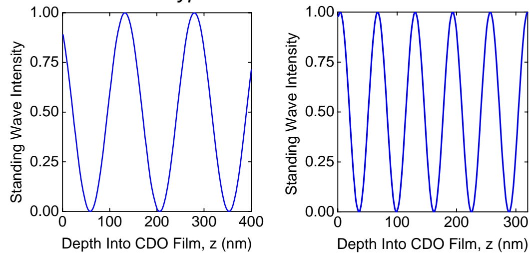
Simple Model: standing wave in a thin film on a perfectly reflecting substrate:

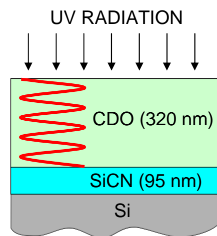
$$I = \alpha \sin^2 k(d - z) \quad \text{with} \quad k = 2\pi n/\lambda$$

where
- α amplitude of the standing-wave
- n film refractive index
- λ wavelength of the incident light
- d film thickness
- z depth into film

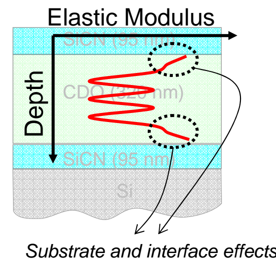
Cuthbert, J. D. *Optical projection printing.* Solid State Technology 50, 59-69 (1977).

Typical values of n and λ

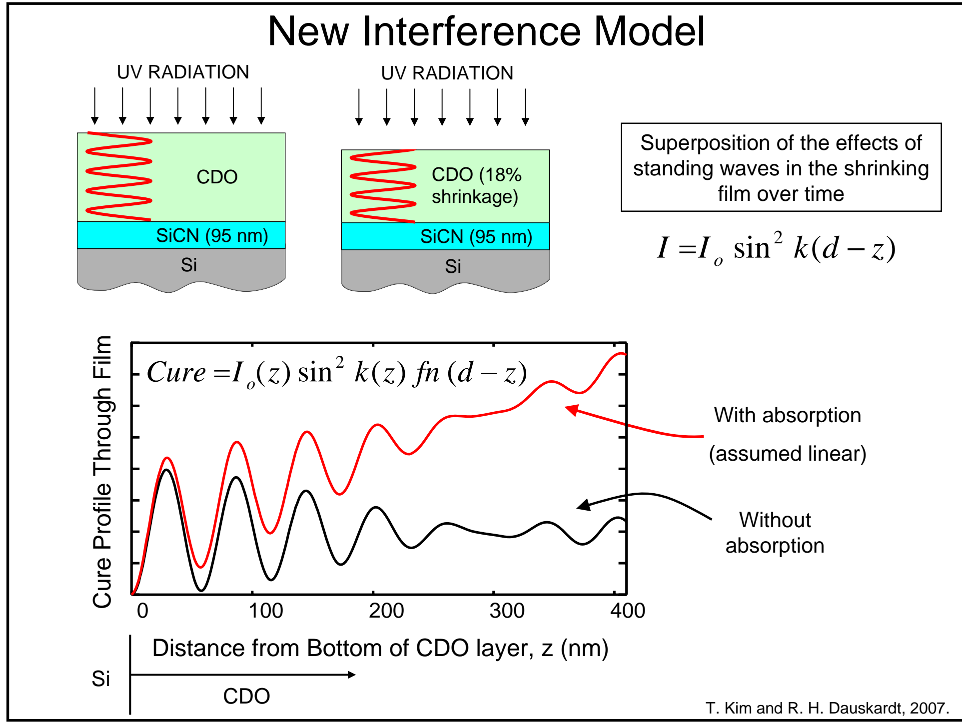


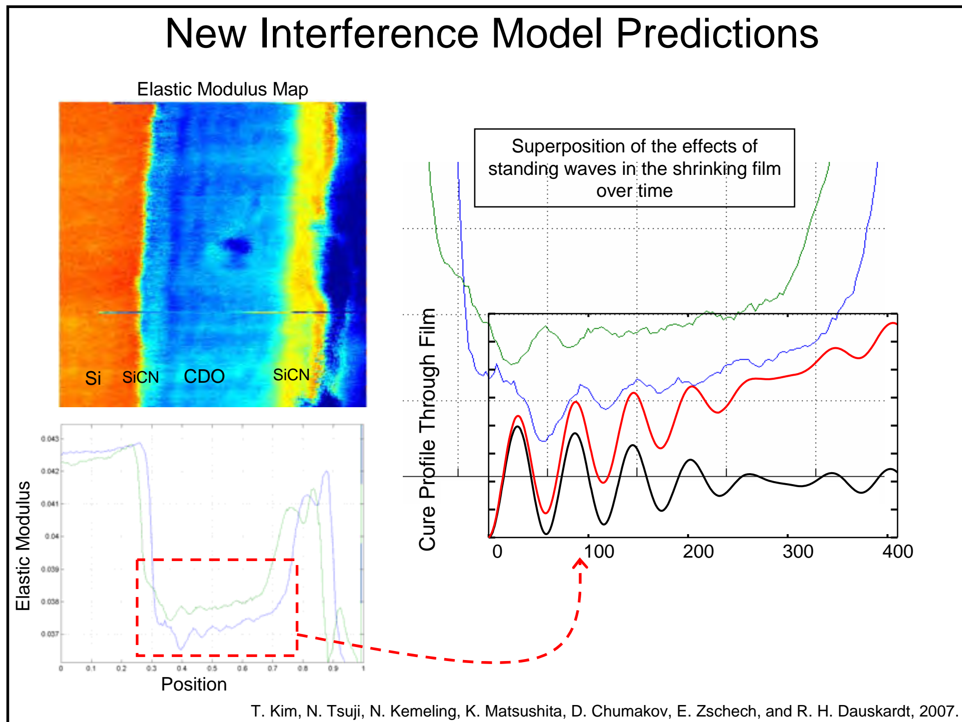


Measurement of modulus variation by FM-AFM

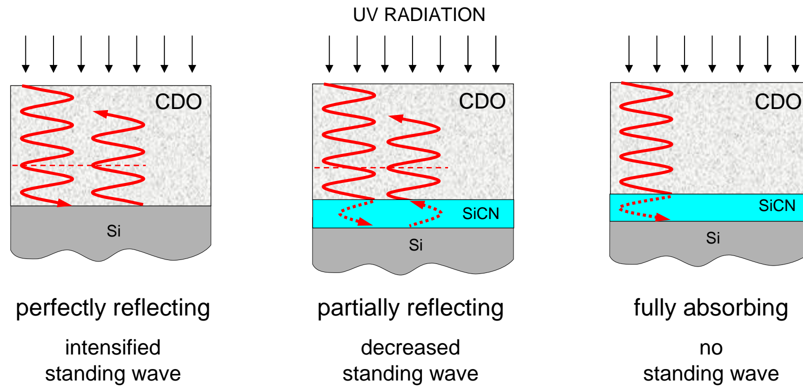


Substrate and interface effects


New Interference Model
UV RADIATION
UV RADIATION
CDO
CDO (18% shrinkage)
SiCN (95 nm)
SiCN (95 nm)
Si
Si
Superposition of the effects of standing waves in the shrinking film over time
$I = I_o \sin^2 k(d-z)$
$Cure = I_o(z) \sin^2 k(z)\, fn\,(d-z)$
Cure Profile Through Film
0
100
200
300
400
Distance from Bottom of CDO layer, z (nm)
Si
CDO
With absorption
(assumed linear)
Without absorption
T. Kim and R. H. Dauskardt, 2007.


New Interference Model Predictions
Elastic Modulus Map
Si
SiCN
CDO
SiCN
Elastic Modulus
Position
Superposition of the effects of standing waves in the shrinking film over time
Cure Profile Through Film
0
100
200
300
400
T. Kim, N. Tsuji, N. Kemeling, K. Matsushita, D. Chumakov, E. Zschech, and R. H. Dauskardt, 2007.

Role of the Bottom SiCN Layer



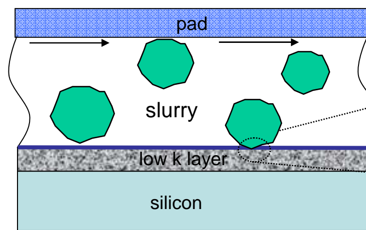
perfectly reflecting	partially reflecting	fully absorbing
intensified standing wave	decreased standing wave	no standing wave

- Reflectivity of bottom interface strongly dependent on underlying layer.
- SiCN thin film can significantly absorb high energy UV light depending on its carbon content

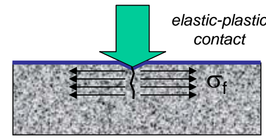
Outline

- Mechanical Reliability of Low-k Materials
  - what is the problem?
  - fracture properties and scaling with density/dielectric constant
- UV Curing Effects on Mechanical Properties
  - fracture path and effects on cohesive and adhesive properties
  - balancing film stress, modulus and fracture properties
- Non-Uniform UV Curing Phenomena
  - evidence for non-uniform curing
  - likely mechanism associated with UV light interference
- CMP Aqueous Chemistry Effects
  - accelerated cracking in aqueous CMP slurries and cleaning solutions
- Die Seal and Crack Stop Structures
  - fracture mechanics approach to preventing dicing damage
- Summary

Mechanics of Damage Initiation and Propagation

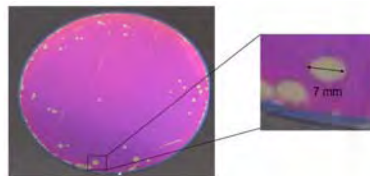


Mode I
crack initiation and propagation



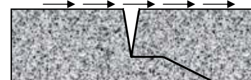
damage created by slurry particle or pad asperity

damage involving low-k film delamination



tractions on film edge of a through cut induce a Mode III component responsible for delamination shape

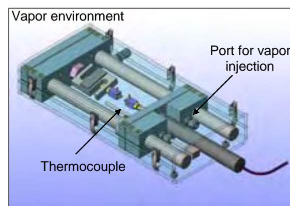
Mode II crack deflection

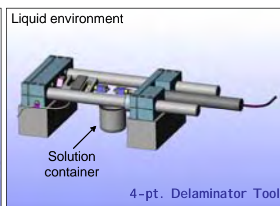


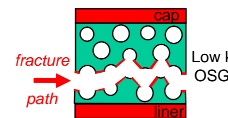
crack kinks to interface for $K_{II} > 0$

crack kinks to surface for $K_{II} < 0$

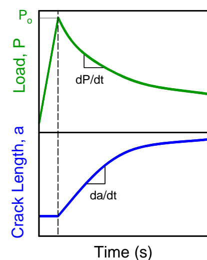
Automated Crack Velocity Testing





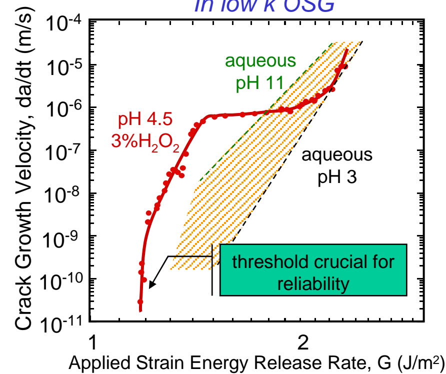


Load Relaxation Crack Growth Technique



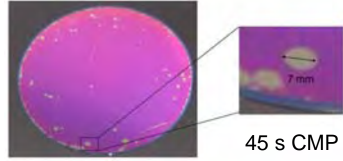
auto analysis

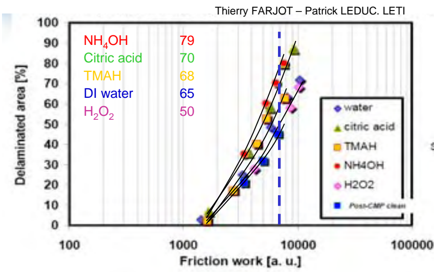
Accelerated Cracking In low k OSG

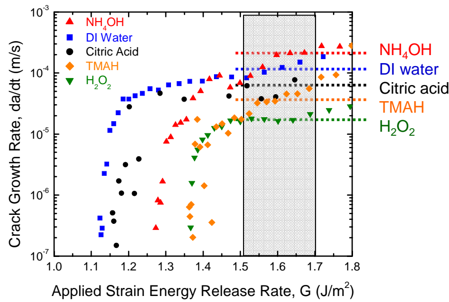


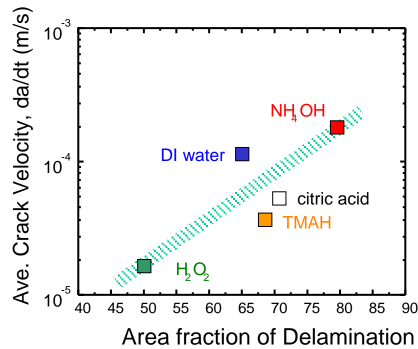
System and support:
DTS Company, Menlo Park, CA (dauskardt@stanford.edu)

Extensive Damage during CMP





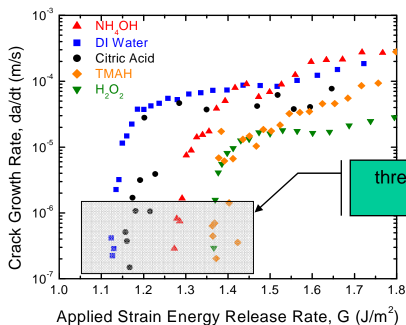




Reduced Damage and High Yield in CMP

- low crack growth rates critical for growth of nano-scale flaws
- dominated by threshold behavior in v-G curves

Crack growth rates $<10^{-10}$ m/s (below threshold) necessary to achieve reliable integration



threshold crucial for reliability

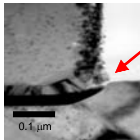
Synergistic effects of CMP slurry chemistry and stress on defect evolution/crack growth are unknown!

Outline

- Mechanical Reliability of Low-k Materials
  - what is the problem?
  - fracture properties and scaling with density/dielectric constant
- UV Curing Effects on Mechanical Properties
  - fracture path and effects on cohesive and adhesive properties
  - balancing film stress, modulus and fracture properties
- Non-Uniform UV Curing Phenomena
  - evidence for non-uniform curing
  - likely mechanism associated with UV light interference
- CMP Aqueous Chemistry Effects
  - accelerated cracking in aqueous CMP slurries and cleaning solutions
- Die Seal and Crack Stop Structures
  - fracture mechanics approach to preventing dicing damage
- Summary

Evolution of Defects control Yield through Processing

- Lower driving force for cracking, G_{total}

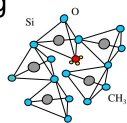


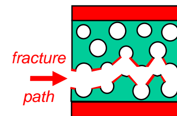
– thin film stresses

– CMP and packaging stress

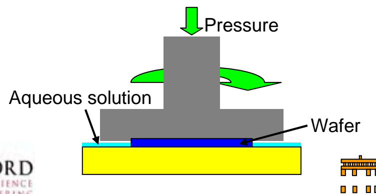
$$G_{total} \leq G_c \; (J/m^2)$$

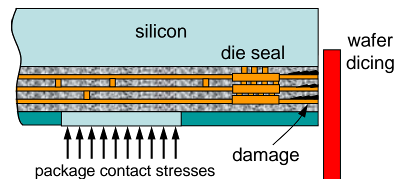
- Optimize resistance to cracking - glass composition, network and pore structure, UV curing





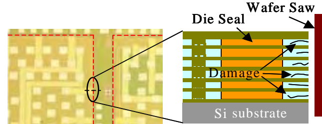
- Control evolution of defects during processing, packaging and service



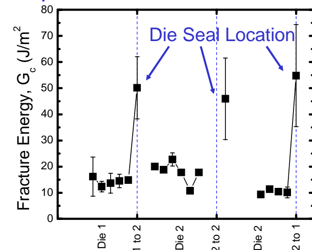


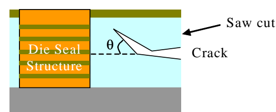
SRC 1391.001: Materials and Interface Innovation for New Concepts in Microelectronic Packaging

Die Seal structures to protect interconnect from saw damage



Improved Fracture Resistance

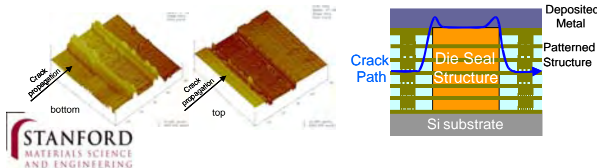


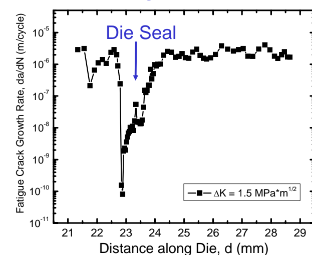


Effectiveness of die seal depends on its ability to deflect cracks

Reduced Fatigue Crack Growth

AFM images of paired fracture surfaces show large deflections around die seals





STANFORD MATERIALS SCIENCE AND ENGINEERING

Summary

- Mechanical Reliability of Low-k Materials
  - what is the problem?
  - fracture properties and scaling with density/dielectric constant
- UV Curing Effects on Mechanical Properties
  - fracture path and effects on cohesive and adhesive properties
  - balancing film stress, modulus and fracture properties
- Non-Uniform UV Curing Phenomena
  - evidence for non-uniform curing
  - likely mechanism associated with UV light interference
- CMP Aqueous Chemistry Effects
  - accelerated cracking in aqueous CMP slurries and cleaning solutions
- Die Seal and Crack Stop Structures
  - fracture mechanics approach to preventing dicing damage
- Summary

STANFORD MATERIALS SCIENCE AND ENGINEERING